

N-Channel Depletion-Mode Vertical DMOS FETs

Features

- High input impedance
- Low input capacitance
- Fast switching speeds
- Low on-resistance
- Free from secondary breakdown
- Low input and output leakage

Applications

- Normally-on switches
- Solid state relays
- Converters
- Linear amplifiers
- Constant current sources
- Power supply circuits
- Telecom

General Description

The Supertex DN3135 is a low threshold depletion-mode (normally-on) transistor utilizing an advanced vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Ordering Information

Part Number	Package Option	Packing		
DN3135K1-G	TO-236AB (SOT-23)	3000/Reel		
DN3135N8-G	TO-243AA (SOT-89)	2000/Reel		

-G denotes a lead (Pb)-free / RoHS compliant package. Contact factory for Wafer / Die availablity. Devices in Wafer / Die form are lead (Pb)-free / RoHS compliant.

Absolute Maximum Ratings

Parameter	Value
Drain-to-source voltage	BV _{DSX}
Drain-to-gate voltage	BV _{DGX}
Gate-to-source voltage	±20V
Operating and storage temperature	-55°C to +150°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

Typical Thermal Resistance

Package	$oldsymbol{ heta}_{j_{oldsymbol{a}}}$
TO-236AB (SOT-23)	203°C/W
TO-243AA (SOT-89)	133°C/W

Product Summary

BV_{DSX}/BV_{DGX}	R _{DS(ON)} (max)	l _{DSS} (min)
350V	35Ω	180mA

Pin Configuration





TO-236AB (SOT-23) TO-2

Product Marking

N1SW W = Code for week sealed = "Green" Packaging

Package may or may not include the following marks: Si or \$\infty\$



W = Code for week sealed
= "Green" Packaging

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TO-243AA (SOT-89)

TO-236AB (SOT-23)

Thermal Characteristics

Package	l _D (continuous) [†]	ן (pulsed)	Power Dissipation @T _A = 25°C	I _{DR} †	I _{DRM}
TO-236AB	72mA	300mA	0.36W	72mA	300mA
TO-243AA	135mA	300mA	1.3W [‡]	135mA	300mA

Notes:

- † $I_{\scriptscriptstyle D}$ (continuous) is limited by max rated $T_{\scriptscriptstyle J}$. ‡ Mounted on FR4 board, 25mm x 25mmx 1.57mm.

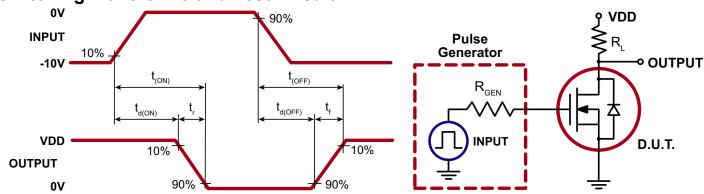
Electrical Characteristics (T_A = 25°C unless otherwise specified)

Sym	Parameter	Min	Тур	Max	Units	Conditions		
BV _{DSX}	Drain-to-source breakdown voltage	350	-	-	V	$V_{GS} = -5.0V, I_{D} = 100\mu A$		
$V_{\rm GS(OFF)}$	Gate-to-source off voltage	-1.5	-	-3.5	V	$V_{DS} = 15V, I_{D} = 10\mu A$		
$\Delta V_{GS(OFF)}$	Change in V _{GS(OFF)} with temperature	-	-	-4.5	mV/°C	$V_{DS} = 15V, I_{D} = 10\mu A$		
I _{GSS}	Gate body leakage current	-	-	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$		
		-	-	1.0	μA	V_{DS} = Max rating, V_{GS} = -5.0V		
l _{D(OFF)}	Drain-to-source leakage current	-	-	1.0	mA	$V_{DS} = 0.8 \text{ Max Rating},$ $V_{GS} = -5.0 \text{V}, T_{A} = 125^{\circ} \text{C}$		
I _{DSS}	Saturated drain-to-source current	180	-	-	mA	$V_{GS} = 0V, V_{DS} = 15V$		
R _{DS(ON)}	Static drain-to-source on-state resistance	-	-	35	Ω	$V_{GS} = 0V$, $I_D = 150mA$		
$\Delta R_{DS(ON)}$	Change in R _{DS(ON)} with temperature		-	1.1	%/°C	$V_{GS} = 0V, I_{D} = 150mA$		
G _{FS}	Forward transconductance	140	-	-	mmho	$V_{DS} = 10V, I_{D} = 100mA$		
C _{ISS}	Input capacitance	-	60	120		V _{GS} = -5.0V,		
C _{oss}	Common source output capacitance	-	6.0	15	pF	$V_{DS}^{00} = 25V,$		
C _{RSS}	Reverse transfer capacitance	-	3.0	10		f = 1.0MHz		
t _{d(ON)}	Turn-on delay time	-	-	10		V _{DD} = 25V,		
t _r	Rise time	-	-	15	no	$I_D = 150 \text{mA},$		
t _{d(OFF)}	Turn-off delay time		-	15	ns	$R_{GEN} = 25\Omega$,		
t _f	Fall time	-	-	20		$V_{GS} = 0v \text{ to } -10V$		
V _{SD}	Diode forward voltage drop	-	-	1.8	V	V _{GS} = -5.0V, I _{SD} = 150mA		
t _{rr}	Reverse recovery time	-	800	-	ns	$V_{GS} = -5.0V, I_{SD} = 150mA$		

Notes:

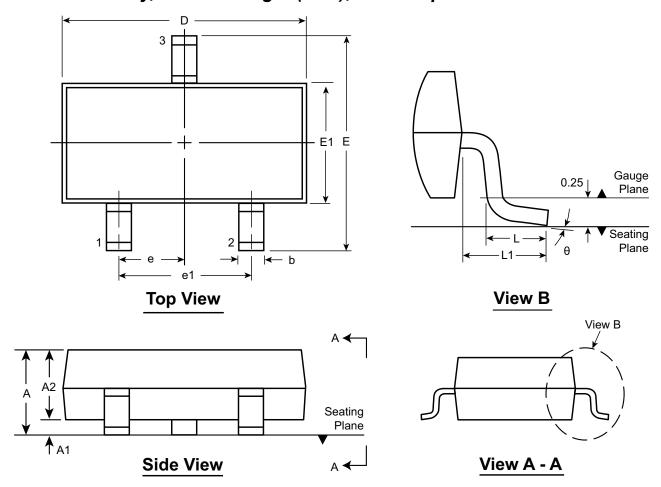
- All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300μs pulse, 2% duty cycle.)
 All A.C. parameters sample tested.

Switching Waveforms and Test Circuit



3-Lead TO-236AB (SOT-23) Package Outline (K1)

2.90x1.30mm body, 1.12mm height (max), 1.90mm pitch



Symb	ol	Α	A1	A2	b	D	Е	E1	е	e1	L	L1	θ
D:	MIN	0.89	0.01	0.88	0.30	2.80	2.10	1.20	0.05	4.00	0.20 [†]	0.54	0 °
(mm)	NOM	_	-	0.95	-	2.90	-	1.30	0.95 BSC	1.90 BSC 0.50	0.54 REF	-	
	MAX	1.12	0.10	1.02	0.50	3.04	2.64	1.40	5		ВЗС	0.60	1,5

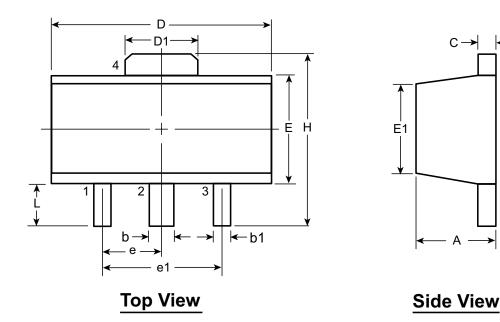
JEDEC Registration TO-236, Variation AB, Issue H, Jan. 1999.

Drawings not to scale.

Supertex Doc.#: DSPD-3TO236ABK1, Version C041309.

[†] This dimension differs from the JEDEC drawing.

3-Lead TO-243AA (SOT-89) Package Outline (N8)



Symbo	ol	Α	b	b1	С	D	D1	Е	E1	е	e1	Н	L	
Dimensions (mm) NOI	MIN	1.40	0.44	0.36	0.35	4.40	1.62	2.29	2.00 [†]	1.50 3.00 BSC BSC			3.94	0.73 [†]
	NOM	-	-	-	-	-	-	-	-		-	-		
	MAX	1.60	0.56	0.48	0.44	4.60	1.83	2.60	2.29			4.25	1.20	

JEDEC Registration TO-243, Variation AA, Issue C, July 1986.

† This dimension differs from the JEDEC drawing

Drawings not to scale.

Supertex Doc. #: DSPD-3TO243AAN8, Version F111010.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to http://www.supertex.com/packaging.html.)

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